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SHA

Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 25 A



PRIMARY CHARACTERISTICS					
I _{T(AV)}	25 A				
V _{DRM} /V _{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V 1200 V				
V _{TM}	1.70 V				
I _{GT}	60 mA				
TJ	-65 °C to +125 °C				
Package	TO-48 (TO-208AA)				
Circuit configuration	Single SCR				

FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High dl/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
		25	А		
I _{T(AV)}	T _C	85	°C		
I _{T(RMS)}		40	А		
1	50 Hz	420	٨		
I _{TSM}	60 Hz	440	— A		
l ² t	50 Hz	867	— A ² s		
1-1	60 Hz	790	A-S		
V _{DRM} /V _{RRM}		100 to 1200	V		
t _q	Typical	110	μs		
TJ		-65 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE	RATINGS			
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$
	10	100	150	20
	20	200	300	
	40	400	500	
VS-25RIA	60	600	700	10
	80	800	900	10
	100	1000	1100	
	120	1200	1300	

Notes

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $^{(2)}$ For voltage pulses with $t_p \leq 5\mbox{ ms}$

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PABAMETER	SYMBOL		TEST COND		VALUES	UNITS	
	STIVIDOL	TEST CONDITIONS					
Maximum average on-state current at case temperature	I _{T(AV)}	180° sinusoi	180° sinusoidal conduction		25 85	A °C	
Maximum RMS on-state current	1				40	-	
Maximum Rivis on-state current	I _{T(RMS)}		T		-	A	
		t = 10 ms	No voltage		420		
Maximum peak, one-cycle	1	t = 8.3 ms	reapplied		440	A	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		350	~	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	370		
		t = 10 ms	No voltage	initial T _J = T _J maximum	867	A ² s	
Maximum I ² t for fusing	121	t = 8.3 ms	reapplied		790		
	l ² t	t = 10 ms	100 % V _{RRM} reapplied		615		
		t = 8.3 ms			560		
Maximum I ² \sqrt{t} for fusing	l²√t		t = 0.1 to 10 ms, no voltage reapplied, T ₁ = T ₁ maximum			A²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		0.99	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$), T _J = T _J maximu	ım	1.40	v	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum				
High level value of on-state slope resistance	r _{t2}	(I > π x I _{T(AV)}), T _J = T _J maximum		5.7	mΩ		
Maximum on-state voltage	V _{TM}	l _{pk} = 79 A, T	_J = 25 °C		1.70	V	
Maximum holding current	l _Η	T _ 05 °O		(registive load	130	m (
Latching current	١L	$I_{\rm J} = 25^{-1}$ C, a	anode supply 6 V	, resistive load	200	mA	

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	V _{DRM} ≤ 600 V		200		
Maximum rate of rise	$V_{DRM} \le 800 \text{ V}$	dl/dt	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$	180	A/µs
of turned-on current	$V_{DRM} \leq 1000 \ V$	ui/ut	t Gate pulse = 20 V, 15 Ω , t _p = 6 µs, t _r = 0.1 µs maximum – I _{TM} = (2 x rated dl/dt) A	160	
$V_{DRM} \le 1600 V$				150	
Typical turn-on time		t _{gt}	T_J = 25 °C, at rated $V_{DRM}/V_{RRM},$ T_J = 125 °C	0.9	
Typical reverse recovery time		t _{rr}	T_J = T_J maximum, I_{TM} = $I_{T(AV)},$ t_p > 200 $\mu s,$ dl/dt = - 10 A/ μs	4	μs
Typical turn-off time		tq	$ \begin{split} T_J = T_J \; maximum, \; I_{TM} = I_{T(AV)}, \; t_p > 200 \; \mu s, \; V_R = 100 \; V, \\ dI/dt = - \; 10 \; A/\mu s, \; dV/dt = 20 \; V/\mu s \; linear \; to \; 67 \; \% \; V_{DRM}, \\ gate \; bias \; 0 \; V \; to \; 100 \; W \end{split} $	110	40

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	100	V/µs
of off-state voltage	uv/ut	$T_J = T_J$ maximum linear to 67 % rated V_{DRM}	300 (1)	v/µs

Note

 $^{(1)}$ Available with: dV/dt = 1000 V/µs, to complete code add S90 i.e. 25RIA120S90

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TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P _{GM}	T T movimum	- - .		W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum		2.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum		1.5	А
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum		10	V
		T _J = - 65 °C		90	mA
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger current/voltage are the lowest	60	
		T _J = 125 °C		35	
		$T_J = -65 \degree C$ value which will trigger all units		3.0	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	6 V anode to cathode applied	2.0	V
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	$T_J = T_J$ maximum, $V_{DRM} =$ Rated value		2.0	mA
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum, V _{DRM} = Rated value	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-65 to +125	°C	
Maximum thermal resistance, junction to case	R _{thJC}	R _{thJC} DC operation		K/W	
Maximum thermal resistance, case to heat sink	R _{thCS}	R _{thCS} Mounting surface, smooth, flat and greased			
		Non-lubricated threads	3.4 ^{+ 0 - 10 %} (30)	N⋅m	
Allowable mounting torque	Lubricated threads		2.3 ^{+ 0 - 10 %} (20)	(lbf · in)	
Approximate weight			14	g	
Approximate weight			0.49	oz.	
Case style		See dimensions - link at the end of datasheet	TO-48 (TO	-208AA)	

$\Delta \mathbf{R}_{thJC}$ CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.17	0.13		
120°	0.21	0.22		
90°	0.27	0.30	$T_J = T_J$ maximum	K/W
60°	0.40	0.42		
30°	0.69	0.70		

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

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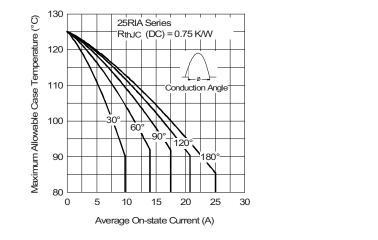


Fig. 1 - Current Ratings Characteristics

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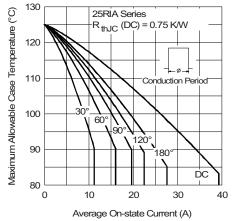


Fig. 1 - Current Ratings Characteristics

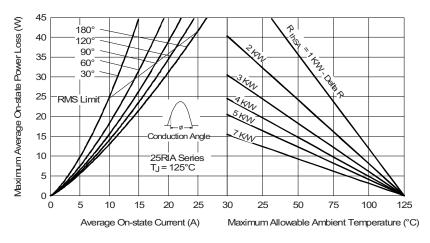
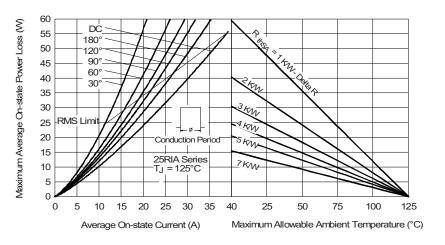


Fig. 2 - On-State Power Loss Characteristics





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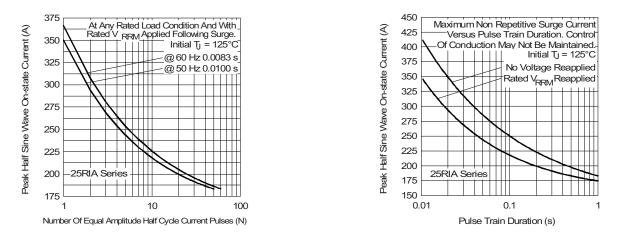
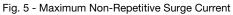


Fig. 4 - Maximum Non-Repetitive Surge Current

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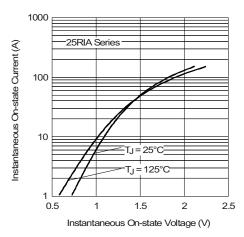


Fig. 6 - Forward Voltage Drop Characteristics

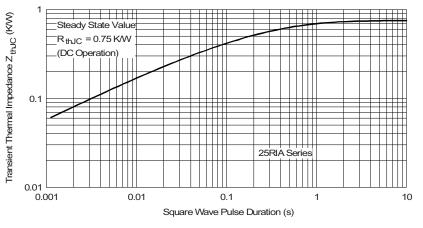


Fig. 7 - Thermal Impedance Z_{thJC} Characteristics

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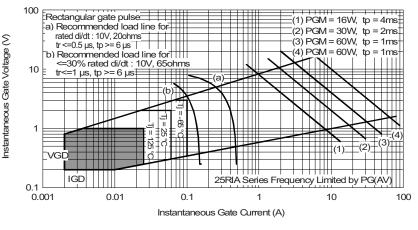


Fig. 8 - Gate Characteristics

ORDERING INFORMATION TABLE

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Device code	VS-	25	RIA	120	М	S90
		2	3	4	5	6
	1 -			nicondu	ctors pro	oduct
	2 - 3 -		rrent coo sential p	de art numl	ber	
	4 -		-	de x 10 :		
	5 -			d base T ase TO-4	``	
	6 -		tical dV/ ne = 300	dt:) V/µs (s	standard	l value)
		S90	0 = 1000) V/µs (s	pecial s	election

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95333			

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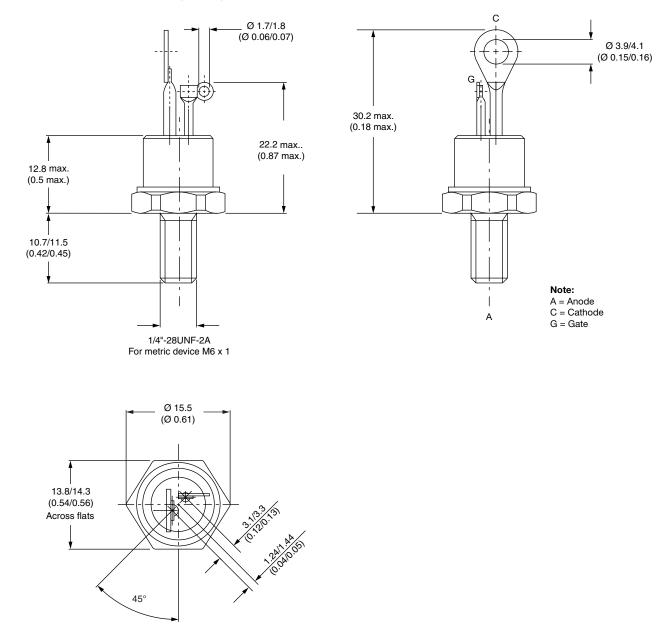


Outline Dimensions

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TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)





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 T1220N22TOF VT
 T201N70TOH
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 TT250N12KOF-K
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